MITSUBISHI GATE TURN-OFF THYRISTORS

FG2000FX-50DA

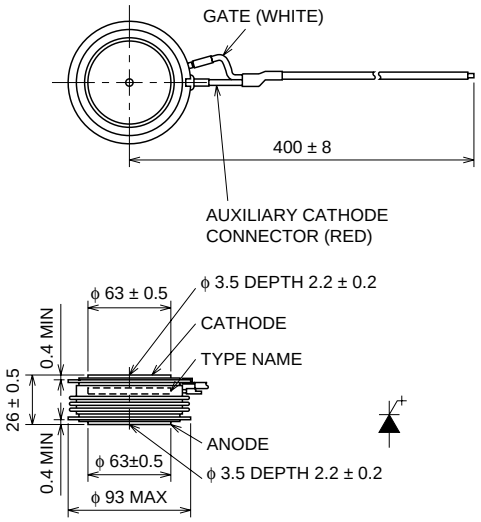
HIGH POWER INVERTER USE
PRESS PACK TYPE

FG2000FX-50DA



- I_{TQRM} Repetitive controllable on-state current 2200A
- $I_{T(AV)}$ Average on-state current 1050A
- V_{DRM} Repetitive peak off state voltage 2500V
- Anode short type

OUTLINE DRAWING Dimensions in mm



APPLICATION

Inverters, D.C. choppers, Induction heaters, D.C. to D.C. converters.

MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
		50DA	
V_{RRM}	Repetitive peak reverse voltage	17	V
V_{RSM}	Non-repetitive peak reverse voltage	17	V
$V_{R(DC)}$	DC reverse voltage	17	V
V_{DRM}	Repetitive peak off-state voltage*	2500	V
V_{DSM}	Non-repetitive peak off-state voltage*	2500	V
$V_{D(DC)}$	DC off-state voltage*	2000	V

* : V_{GK} = –2V

Symbol	Parameter	Conditions	Ratings	Unit
I_{TQRM}	Repetitive controllable on-state current	V_{DM} = 1875V, T_j = 125°C, C_S = 4.0μF, L_S = 0.3μH	2200	A
$I_{T(RMS)}$	RMS on-state current		1650	A
$I_{T(AV)}$	Average on-state current	f = 60Hz, sine wave θ = 180°, T_f = 73°C	1050	A
I_{TSM}	Surge (non-repetitive) on-state current	One half cycle at 60Hz	16	kA
I^2t	Current-squared, time integration	One cycle at 60Hz	10.5×10^5	A^2s
di_T/dt	Critical rate of rise of on-state current	V_D = 1250V, I_{GM} = 30A, T_j = 125°C	1000	A/μs
V_{FGM}	Peak forward gate voltage		10	V
V_{RGM}	Peak reverse gate voltage		17	V
I_{FGM}	Peak forward gate current		100	A
I_{RGM}	Peak gate reverse current		650	A
P_{FGM}	Peak forward gate power dissipation		280	W
P_{RGM}	Peak reverse gate power dissipation		18	kW
$P_{FG(AV)}$	Average forward gate power dissipation		50	W
$P_{RG(AV)}$	Average reverse gate power dissipation		150	W
T_j	Junction temperature		–40 ~ +125	°C
T_{stg}	Storage temperature		–40 ~ +150	°C
—	Mounting force required	Recommended value 20	18 ~ 24	kN
—	Weight	Standard value	760	g

MITSUBISHI ELECTRIC

FG2000FX-50DA

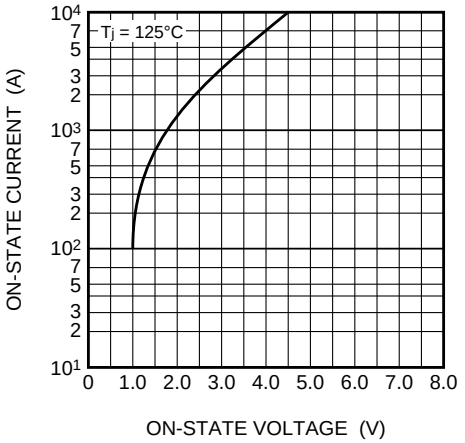
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PRESS PACK TYPE

ELECTRICAL CHARACTERISTICS

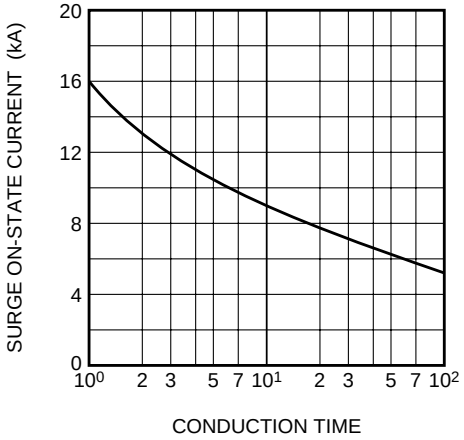
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V_{TM}	On-state voltage	T_j = 125°C, I_{TM} = 2000A, Instantaneous measurment	—	—	2.4	V
I_{RRM}	Repetitive peak reverse current	T_j = 125°C, V_{RRM} Applied	—	—	50	mA
I_{DRM}	Repetitive peak off-state current	T_j = 125°C, V_{DRM} Applied, V_{GK} = –2V	—	—	50	mA
I_{RG}	Reverse gate current	T_j = 125°C, V_{RG} = 17V	—	—	50	mA
dv/dt	Critical rate of rise of off-state voltage	T_j = 125°C, V_D = 1250V, V_{GK} = –2V	1000	—	—	V/µs
t_{gt}	Turn-on time	T_j = 125°C, I_{TM} = 2200A, I_{GM} = 30A, V_D = 1250V	—	—	10	µs
t_{gq}	Turn-off time	T_j = 125°C, I_{TM} = 2200A, V_{DM} = 1875V, di_{GQ}/dt = –30A/µs V_{RG} = 17V, C_S = 4.0µF, L_S = 0.3µH	—	—	30	µs
I_{GQM}	Peak gate turn-off current		—	610	—	A
V_{GT}	Gate trigger voltage	DC METHOD : V_D = 24V, R_L = 0.1Ω, T_j = 25°C	—	—	1.5	V
I_{GT}	Gate trigger current		—	—	2500	mA
$R_{th(j-f)}$	Thermal resistance	Junction to fin	—	—	0.017	°C/W

PERFORMANCE CURVES

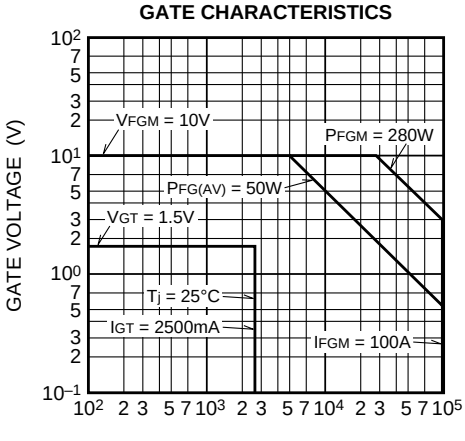
MAXIMUM ON-STATE CHARACTERISTIC



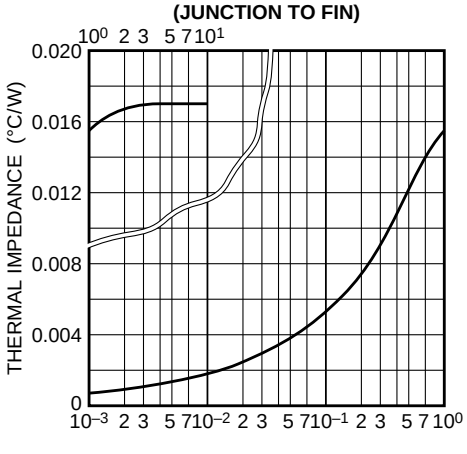
RATED SURGE ON-STATE CURRENT



GATE CHARACTERISTICS



MAXIMUM THERMAL IMPEDANCE CHARACTERISTIC (JUNCTION TO FIN)

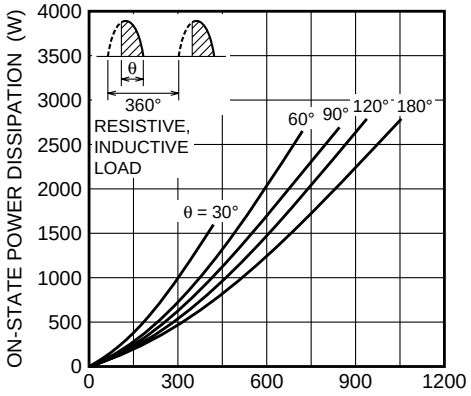


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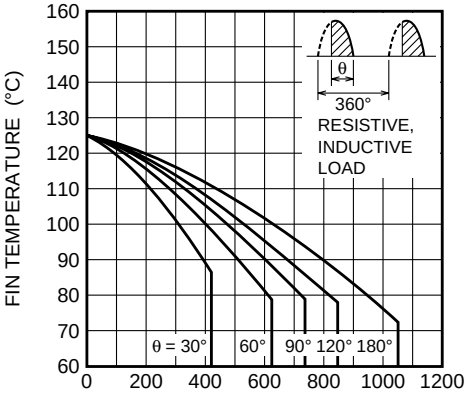
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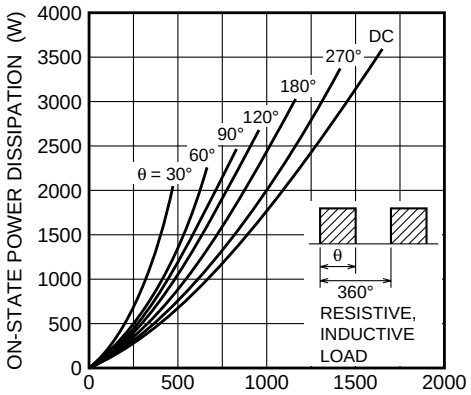
MAXIMUM ON-STATE POWER DISSIPATION CHARACTERISTICS (SINGLE-PHASE HALF WAVE)



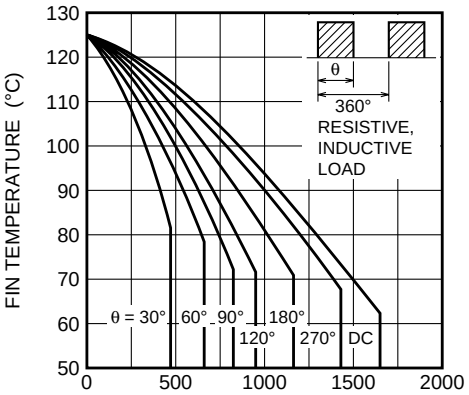
ALLOWABLE FIN TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



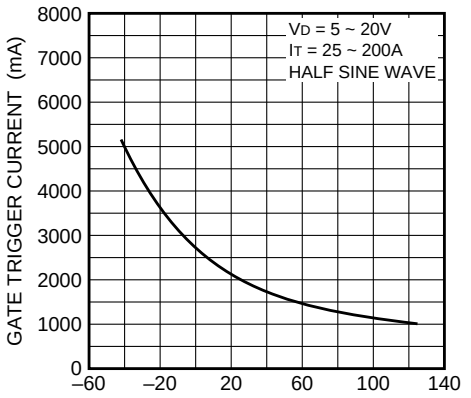
MAXIMUM ON-STATE POWER DISSIPATION CHARACTERISTICS (RECTANGULAR WAVE)



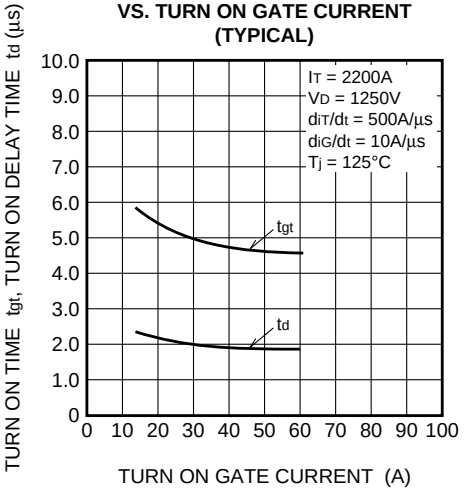
ALLOWABLE FIN TEMPERATURE VS. AVERAGE ON-STATE CURRENT (RECTANGULAR WAVE)



GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE (TYPICAL)

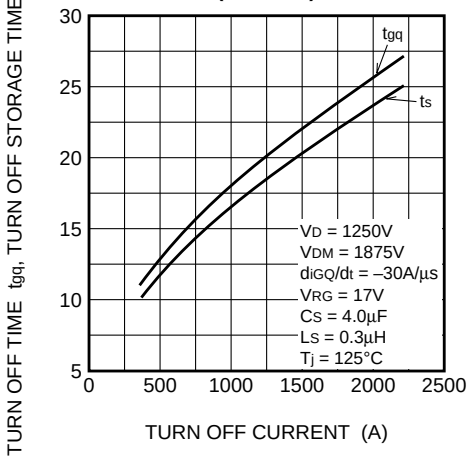


TURN ON TIME, TURN ON DELAY TIME VS. TURN ON GATE CURRENT (TYPICAL)

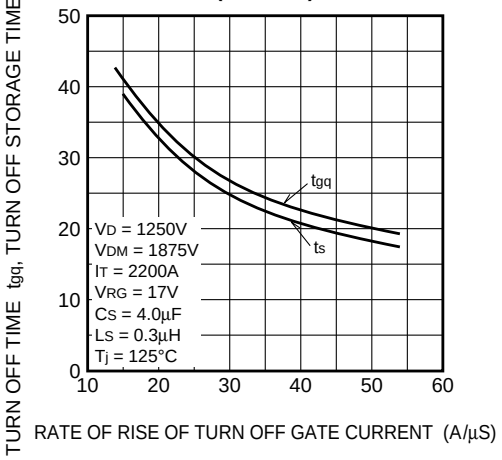


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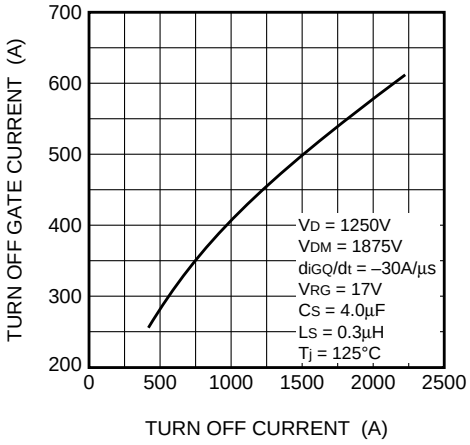
TURN OFF TIME, TURN OFF STORAGE TIME VS. TURN OFF CURRENT (TYPICAL)



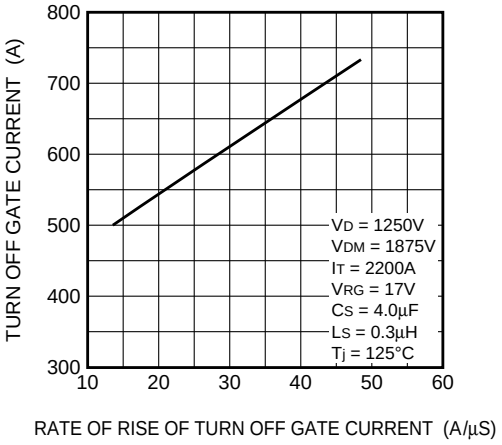
TURN OFF TIME, TURN OFF STORAGE TIME VS. RATE OF RISE OF TURN OFF GATE CURRENT (TYPICAL)



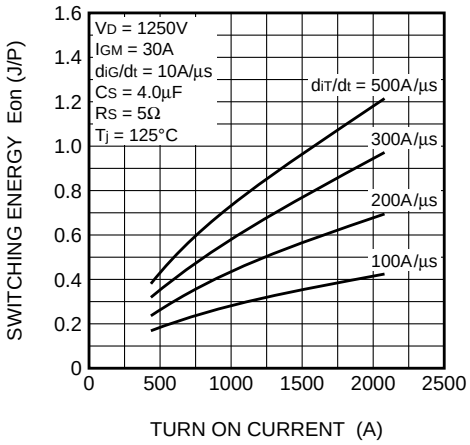
TURN OFF GATE CURRENT VS. TURN OFF CURRENT (TYPICAL)



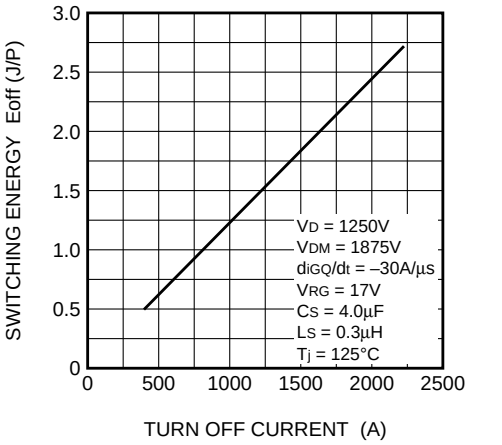
TURN OFF GATE CURRENT VS. RATE OF RISE OF GATE CURRENT (TYPICAL)



TURN ON SWITCHING ENERGY (MAXIMUM)



TURN OFF SWITCHING ENERGY (MAXIMUM)



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ООО «НИОКР СИТЕМС»
Москва, 125362, Россия, ул. Вишневая, д. 9, к. 1, Блок 104 а и 104 в

Телефон: 8 (495) 268-14-82
Email: n@nsistems.ru

ИНН: 7735154786
ОГРН: 1167746717709